

Appl. No. 10/712,876
Amft. Dated: June 12, 2006
Reply to Office Action of March 10, 2006

AMENDMENTS TO THE ABSTRACT:

Please replace the abstract with the following amended abstract:

Provided is a method of depositing a thin film using a hafnium compound. The method includes depositing a primary thin film and depositing a secondary thin film. The depositing of the primary thin film and the depositing of the secondary thin film are repeated once or more. The depositing of the primary thin film includes feeding a first reactive gas, purging the first reactive gas, feeding a third reactive gas, and purging the third reactive gas, and repeating the aforementioned steps a first plurality of (N) times. The feeding of the first reactive gas includes feeding a second reactive gas, purging the second reactive gas, feeding the third reactive gas, and purging the third reactive gas, and repeating the aforementioned steps a second plurality of (M) times.